

## 2.5-GHz Quadrature Up-Converter

### Description

The U2891B is a silicon monolithic IC made with TEMIC Semiconductors' advanced UHF process.

The IC consists of a 500-MHz I/Q quadrature modulator and a 2.5-GHz mixer. Both parts can be connected via an external filter in order to suppress harmonics and spurious products. The device features 3-V operation, low-current consumption and furthermore two separate power-down functions for modulator and mixer. The RF ports are single-ended and the device can be operated adjustment

free. These features and the double-conversion concept of U2891B make this device perfectly suited for all digital radio applications from 900 MHz up to 2.5 GHz (e.g., GSM, DCS 1800, JDC, PHP and WLAN).

Electrostatic sensitive device.

Observe precautions for handling.



### Features

- Low power consumption: 25 mA / 3 V (typical at -8 dBm output level)
- 2.5 GHz output frequency
- Excellent sideband suppression by means of duty cycle regeneration and 90° phase control
- Separate power-down mode for modulator and mixer
- Low LO input level: -10 dBm (typical)
- LO and RF port 50-Ω single-ended

### Benefits

- Extended talk time due to increased battery life
- Few external components results in cost and board space saving
- Adjustment free, hence saves time and cost
- One TX platform for different systems
- Reduced costs and space for battery (3-V operation)

### Block Diagram

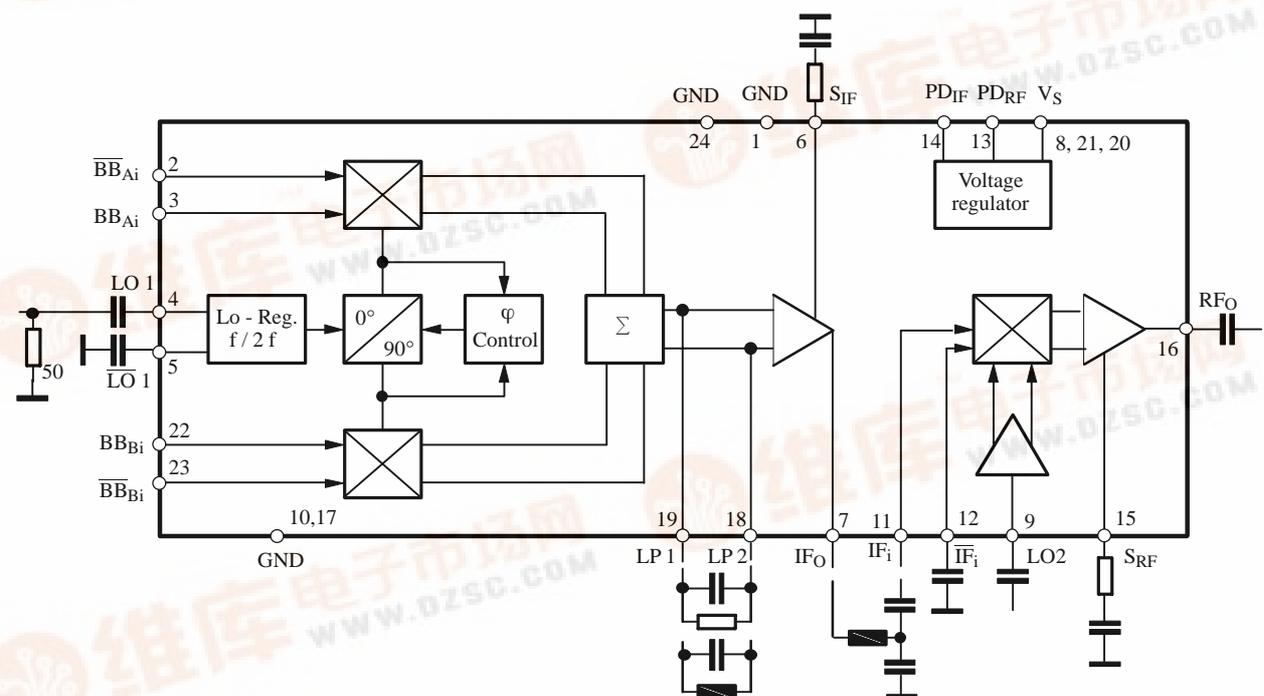
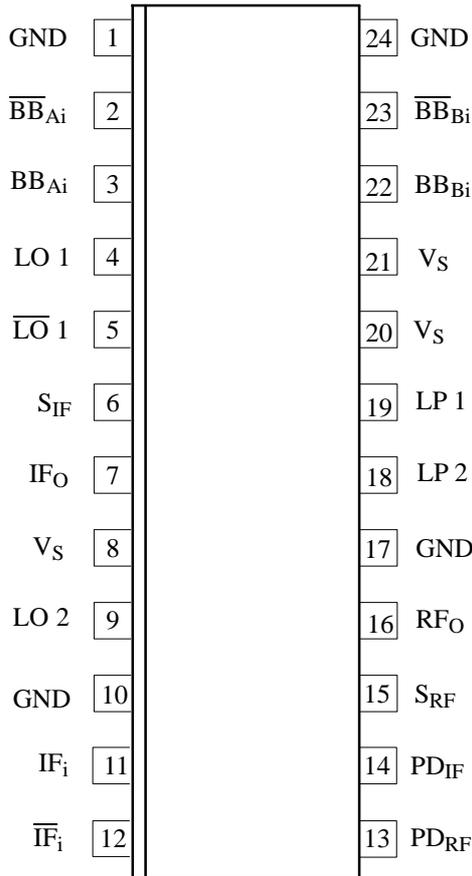


Figure 1. Block diagram

## Ordering Information

Extended Type Number	Package	Remarks
U2891B-MFS	SSO24	Tube, MOQ 690 pcs.
U2891B-MFSG3	SSO24	Taped and reeled, MOQ 4000 pcs.

## Pin Description



94 8581 e

Pin	Symbol	Function
1	GND	Ground
2	$\overline{BB}_{Ai}$	Baseband input A inverse
3	$BB_{Ai}$	Baseband input A
4	LO 1	LO 1 input
5	$\overline{LO} 1$	LO 1 input inverse
6	$S_{IF}$	Output symmetry IF
7	$IF_O$	IF output
8	$V_S$	Supply voltage
9	LO 2	LO 2 input
10	GND	Ground
11	$IF_i$	IF input
12	$\overline{IF}_i$	IF input inverse
13	$PD_{RF}$	Power-down RF
14	$PD_{IF}$	Power-down IF
15	$S_{RF}$	Output symmetry RF
16	$RF_O$	RF output
17	GND	Ground
18	LP 2	Filter and IF level adjustment
19	LP 1	Filter and IF level adjustment
20	$V_S$	Supply voltage
21	$V_S$	Supply voltage
22	$BB_{Bi}$	Baseband input B
23	$\overline{BB}_{Bi}$	Baseband input B inverse
24	GND	Ground

## Absolute Maximum Ratings

Parameters	Symbol	Value	Unit
Supply voltage Pins 8, 20 and 21	$V_S, V_{SRF}$	6	V
Input voltage Pins 2, 3, 4, 5, 9, 11, 12, 22 and 23	$V_i$	0 to $V_S$	V
Junction temperature	$T_j$	125	°C
Storage temperature range	$T_{stg}$	-40 to +125	°C

## Operating Range

Parameters	Symbol	Value	Unit
Supply voltage Pins 8, 20 and 21	$V_S, V_{SRF}$	2.7 to 5.5	V
Ambient temperature range	$T_{amb}$	-40 to +85	°C

## Thermal Resistance

Parameters	Symbol	Value	Unit
Junction ambient SSO24	$R_{thJA}$	140	K/W

## Electrical Characteristics: General Data

Parameters	Test Conditions / Pin	Symbol	Min.	Typ.	Max.	Unit
<b>Power supply</b>						
Supply voltage range	Pin 8, 20 and 21	$V_S, V_{SRF}$	2.7		5.5	V
Supply current	Pin 8, 20 and 21, $V_S = 3$ V	$I_S, I_{SRF}$		25		mA

## Electrical Characteristics: I/Q Modulator

Test conditions (unless otherwise specified):  $V_S = 3$  V,  $T_{amb} = 25^\circ\text{C}$ , referred to test circuit.  
System impedance  $Z_o = 50 \Omega$ ,  $f_{LO1} = 100$  MHz,  $P_{LO1} = -10$  dBm.

Parameters	Test Conditions / Pin	Symbol	Min.	Typ.	Max.	Unit
<b>IF output Pin 7</b>						
Output level	$R_{LP} = \infty$	$P_{IFo}$		-8		dBm
LO1 suppression		$LO_{RFo}$		40		dB
Voltage standing wave ratio		$VSWR_{IFo}$		1.4	2	
Sideband suppression		$SBS_{IFo}$		45		dB
<b>Baseband inputs Pins 2, 3, 22 and 23</b>						
Input voltage range (differential)		$V_{BBi}$		500	900	mVpp
Input impedance		$Z_{BBi}$		150		k $\Omega$
Input frequency		$f_{BBi}$			200	MHz
<b>LO1 input Pins 4 and 5</b>						
Frequency range		$f_{LOi}$	30		500	MHz
Input level <sup>1)</sup>		$P_{LOi}$		-10	-2	dBm
Input impedance		$Z_{iLO}$		tbd.		$\Omega$
Duty cycle range		$DCR_{LO1}$	0.4		0.6	
<b>Power-down mode</b>						
Supply current	$V_{PD} \leq 0.5$ V Pin 14	$I_{PD}$		<5		$\mu\text{A}$
Settling time	$C_{SPD} = 100$ pF, $C_{LO} = 100$ pF, $C_{RFo} = 1$ nF	$t_S$		10		$\mu\text{s}$
<b>Power down voltage Pin 14</b>						
“Power on”	$V_S = 3.5$ to $5.5$ V $V_S = 2.7$ to $3.5$ V	$V_{PON}$	$V_S - 0.5$ $V_S$		$V_S + 0.5$ $V_S + 0.5$	V V
“Power down”		$V_{PDN}$			1	V
Power down current	Power on Power down	$I_{PON}$ $I_{PDN}$		0.15 < 1		mA $\mu\text{A}$

Note:

<sup>1)</sup> Required LO level is a function of the LO frequency

## Electrical Characteristics: Mixer

$V_S = 3\text{ V}$ ,  $f_{LO2} = 800\text{ MHz}$ ,  $f_{IF} = 100\text{ MHz}$ ,  $P_{LO2} = -10\text{ dBm}$ , system impedance  $Z_o = 50\ \Omega$ ,  $T_{amb} = 25\text{ }^\circ\text{C}$ , reference point Pin 10, unless otherwise specified

Parameters	Test Conditions / Pin	Symbol	Min.	Typ.	Max.	Unit
<b>Operating frequencies</b>						
RF <sub>O</sub> frequency	Pin 16	RF <sub>O</sub>	50		2500	MHz
LO2 frequency	Pin 9	f <sub>LO2</sub>	50		2500	MHz
<b>Isolation</b>						
LO2 spurious at RF <sub>O</sub>	Pin 9–16 P <sub>iLO</sub> = -10 to 0 dBm	IS <sub>LO2-RF<sub>O</sub></sub>		-30		dBm
RF <sub>O</sub> to LO2	Pin 16–9	IS <sub>RF<sub>O</sub>-LO2</sub>		tbd.		dB
<b>Output level</b>						
Output compression point	Pin 16 R <sub>P0</sub> = ∞	CP <sub>0</sub> - 1 dB		-7		dBm
<b>Input level</b>						
Input compression point <sup>1)</sup>	Pins 11 and 12	CP <sub>i</sub> - 1dB		-15		dBm
Input LO2	Pin 9	P <sub>LO2</sub>		-10		dBm
Third order input intercept point <sup>1)</sup>	Pins 11 and 12	P <sub>IIP3</sub>		-6		dBm
<b>Voltage standing wave ratio (VSWR)</b>						
Input IF	Pins 11 and 12	VSWR <sub>IFi</sub>		tbd.		
Input LO2	Pin 9	VSWR <sub>LO2</sub>		tbd.		
Output RF	Pin 16	VSWR <sub>RF</sub>		tbd.		
Conversion power gain	R <sub>L</sub> = 50 Ω	PG <sub>C</sub>		9		dB
Noise Figure (SSB) <sup>2)</sup>	P <sub>iLO</sub> = -6 dBm	NF50		13		dB
<b>Power-down mode</b>						
Supply current	V <sub>PD</sub> ≤ 0.5 V Pin 13	I <sub>PD</sub>		<5		μA
Settling time	C <sub>SPD</sub> 100 pF, C <sub>LO</sub> = 100 pF, C <sub>RF0</sub> = 1 nF	t <sub>S</sub>		10		μs
<b>Power down voltage Pin 13</b>						
“Power on”	V <sub>S</sub> = 3.5 to 5.5 V V <sub>S</sub> = 2.7 to 3.5 V	V <sub>PON</sub>	V <sub>S</sub> - 0.5 V <sub>S</sub>		V <sub>S</sub> + 0.5 V <sub>S</sub> + 0.5	V V
“Power down”		V <sub>PDN</sub>			1	V
Power down current	Power on Power down	I <sub>PON</sub> I <sub>PDN</sub>		0.15 < 1		mA μA

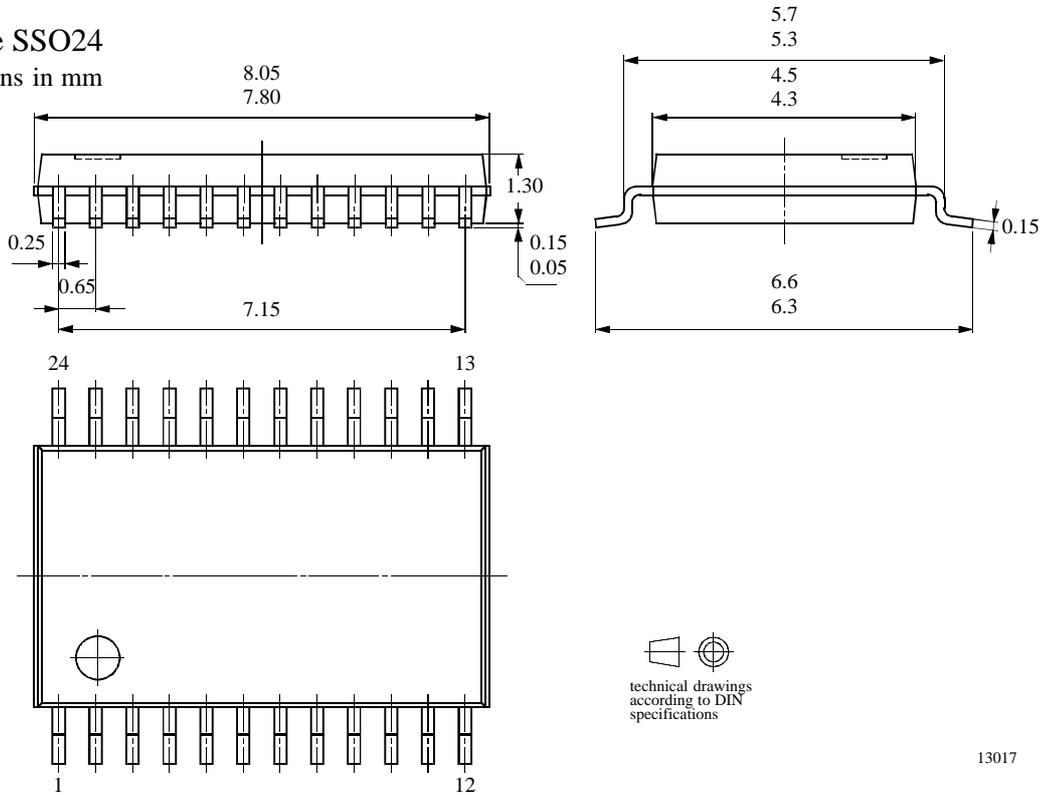
Note:

- 1) with 50 Ω termination resistor at Pin 11
- 2) without termination resistor

**Packing Information**

Package SSO24

Dimensions in mm



13017

## Ozone Depleting Substances Policy Statement

It is the policy of **TEMIC Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify TEMIC Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

**Data sheets can also be retrieved from the Internet: <http://www.temic-semi.com>**

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